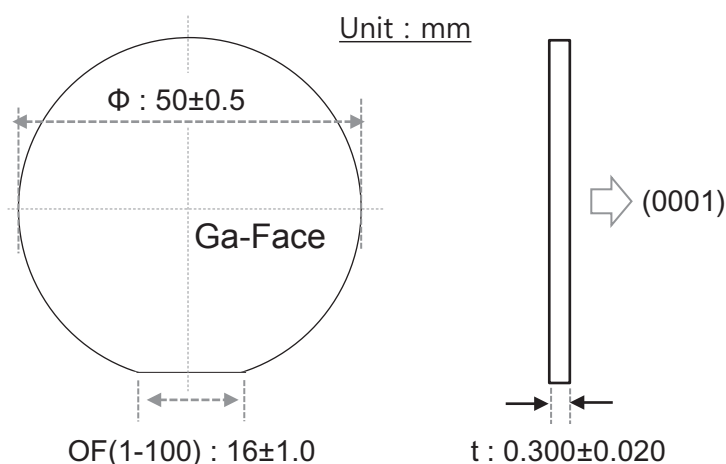
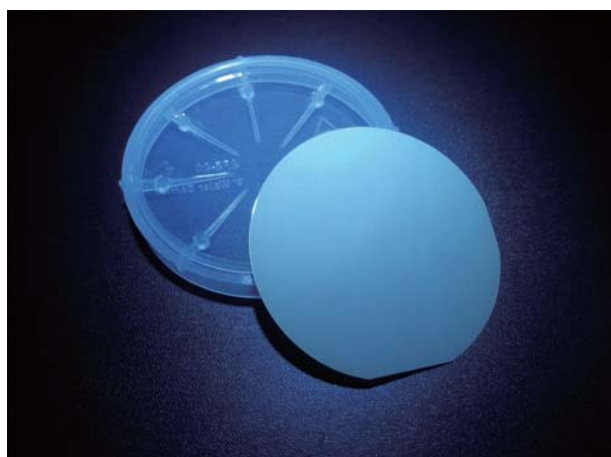


GaN Wafers for LED



Contents	Specifications
Orientation	$(0001) \pm 0.5^\circ$
Diameter	50 ± 0.5 mm
Thickness	300 ± 20 μ m
Conduction Type	N - Type
Carrier Concentration	$\text{mid} \times 10^{17} / \text{cm}^3$
OF Length	16 ± 1.0 mm
Macroscopic Defect Density	$< 50 / 2\text{inch}$
Bow	± 30 μ m
Etch Pit Density	Ave. $< 1 \times 10^7 / \text{cm}^2$
XRD FWHM	$(0002) \ \& \ (10-12) < 100\text{arcsec}$
Surface Finish	Epi - ready, Single side polished
Ra : AFM (10x10 μ m)	< 0.5 nm
Package	Individual Container

